# July 1998

# 54ABT244 Octal Buffer/Line Driver with TRI-STATE® Outputs

# **General Description**

The 'ABT244 is an octal buffer and line driver with TRI-STATE outputs designed to be employed as a memory and address driver, clock driver, or bus-oriented transmitter/ receiver.

#### Features

- Non-inverting buffers
- Output sink capability of 48 mA, source capability of 24 mA
- Output switching specified for both 50 pF and 250 pF loads

# **Ordering Code**

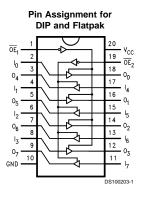
- Guaranteed simultaneous switching, noise level and dynamic threshold performance
- Guaranteed latchup protection
- High impedance glitch free bus loading during entire power up and power down cycle
- Nondestructive hot insertion capability
- Disable time less than enable time to avoid bus contention
- Standard Microcircuit Drawing (SMD) 5962-9214701
- Military
   Package Number
   Package Description

   54ABT244J-QML
   J20A
   20-Lead Ceramic Dual-In-Line

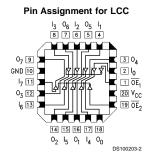
   54ABT244W-QML
   W20A
   20-Lead Cerpack

   54ABT244E-QML
   E20A
   20-Lead Ceramic Leadless Chip Carrier, Type C

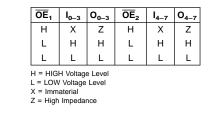
#### **Connection Diagrams**



Pin	Description			
Names				
$\overline{\text{OE}}_1, \overline{\text{OE}}_2$	Output Enable Input			
	(Active Low)			
I <sub>0</sub> -I <sub>7</sub>	Inputs			
O <sub>0</sub> -O <sub>7</sub>	Outputs			



#### **Truth Table**



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# Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Storage Temperature Ambient Temperature under Bias	–65°C to +150°C –55°C to +125°C
Junction Temperature under Bias	
Ceramic	–55°C to +175°C
V <sub>CC</sub> Pin Potential to Ground Pin	-0.5V to +7.0V
Input Voltage (Note 2)	-0.5V to +7.0V
Input Current (Note 2)	-30 mA to +5.0 mA
Voltage Applied to Any Output	
in the Disabled or	
Power-Off State	-0.5V to 5.5V
in the HIGH State	–0.5V to $V_{\text{CC}}$

Current Applied to Output twice the rated  $\rm I_{OL}$  (mA) in LOW State (Max) DC Latchup Source Current –500 mA Over Voltage Latchup (I/O)

10V

# **Recommended Operating** Conditions

–55°C to +125°C
+4.5V to +5.5V
$(\Delta V/\Delta t)$
50 mV/ns
20 mV/ns

# **DC Electrical Characteristics**

Symbol	Parameter		ABT244		Units	V <sub>cc</sub>	Conditions	
			Min	Тур	Max	1		
VIH	Input HIGH Voltage		2.0			V		Recognized HIGH Signal
VIL	Input LOW Voltage				0.8	V		Recognized LOW Signal
V <sub>CD</sub>	Input Clamp Diode Vo	oltage			-1.2	V	Min	$I_{IN} = -18 \text{ mA}$
V <sub>OH</sub>	Output HIGH Voltage	54ABT	2.5			V	Min	I <sub>OH</sub> = -3 mA
		54ABT	2.0			V	Min	I <sub>OH</sub> = -24 mA
V <sub>OL</sub>	Output LOW Voltage	54ABT			0.55	V	Min	I <sub>OL</sub> = 48 mA
I <sub>IH</sub>	Input HIGH Current				5	μA	Max	V <sub>IN</sub> = 2.7V (Note 4)
					5			$V_{IN} = V_{CC}$
I <sub>BVI</sub>	Input HIGH Current B	reakdown Test			7	μA	Max	V <sub>IN</sub> = 7.0V
I <sub>IL</sub>	Input LOW Current				-5	μA	Max	V <sub>IN</sub> = 0.5V (Note 4)
					-5			V <sub>IN</sub> = 0.0V
V <sub>ID</sub>	Input Leakage Test		4.75			V	0.0	I <sub>ID</sub> = 1.9 μA
								All Other Pins Grounded
I <sub>ozh</sub>	Output Leakage Curre	ent			50	μA	0 – 5.5V	$V_{OUT} = 2.7V; \overline{OE}_n = 2.0V$
I <sub>OZL</sub>	Output Leakage Curre	ent			-50	μA	0 – 5.5V	$V_{OUT} = 0.5V; \overline{OE}_n = 2.0V$
los	Output Short-Circuit C	Current	-100		-275	mA	Max	V <sub>OUT</sub> = 0.0V
$I_{CEX}$	Output High Leakage	Current			50	μA	Max	$V_{OUT} = V_{CC}$
$I_{zz}$	Bus Drainage Test				100	μA	0.0	V <sub>OUT</sub> = 5.5V; All Others GND
I <sub>CCH</sub>	Power Supply Curren	t			50	μA	Max	All Outputs HIGH
I <sub>CCL</sub>	Power Supply Curren	t			30	mA	Max	All Outputs LOW
I <sub>ccz</sub>	Power Supply Curren	t			50	μA	Max	$\overline{OE}_n = V_{CC};$
								All Others at $V_{CC}$ or Ground
I <sub>CCT</sub>	Additional I <sub>CC</sub> /Input	Outputs Enabled			2.5	mA	Max	$V_{I} = V_{CC} - 2.1V$
		Outputs TRI-STATE			2.5	mA		Enable Input V <sub>I</sub> = V <sub>CC</sub> – 2.1V
		Outputs TRI-STATE			50	μA		Data Input V <sub>I</sub> = V <sub>CC</sub> – 2.1V
								All Others at $V_{CC}$ or Ground
I <sub>CCD</sub>	Dynamic I <sub>CC</sub>	No Load				mA/	Max	Outputs Open
	(Note 4)				0.1	MHz		$\overline{OE}_n = GND$ , (Note 3)
								One Bit Toggling, 50% Duty Cycle

Note 1: Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: Either voltage limit or current limit is sufficient to protect inputs.

Note 3: For 8 bits toggling, I<sub>CCD</sub> < 0.8 mA/MHz.

Note 4: Guaranteed, but not tested.

Symbol	Pa	arameter	:	54ABT	Units	Fig.	
			T <sub>A</sub> = -5	5°C to +125°C		No.	
			V <sub>cc</sub> =	= 4.5V–5.5V			
				= 50 pF			
			Min	Мах			
t <sub>PLH</sub>	Propaç	pation Delay	1.0	5.3	ns	Figure 5	
t <sub>PHL</sub>	Data to	o Outputs	1.0	5.0			
t <sub>PZH</sub>	Output	Enable	0.8	6.5	ns	Figure 4	
t <sub>PZL</sub>	Time		1.2	7.9			
t <sub>PHZ</sub>	Output	Disable	1.2	7.6	ns	Figure 4	
t <sub>PLZ</sub>	Time		1.0	7.9			
Input Cap		Input Capacitance	9	5.0	pF	$V_{\rm CC} = 0V$	
Input C		Input Capacitance	<u>,</u>	5.0	nF		
C <sub>OUT</sub> (Note 5)		Output Capacitan uency f = 1 MHz, per MII	се	9.0	pF	$V_{CC} = 5.0V$	
Note 5: C <sub>OUT</sub> is	measured at freq t <sub>PLH</sub> vs Te	Output Capacitan	ce	9.0 012. t <sub>PHL</sub> vs		V <sub>CC</sub> = 5.0V	
Note 5: C <sub>OUT</sub> is	measured at freq t <sub>PLH</sub> vs Te	Output Capacitan uency f = 1 MHz, per MII	ce	9.0 0012. C <sub>L</sub> = 50 p	pF	V <sub>CC</sub> = 5.0V	
6.00	measured at freq t <sub>PLH</sub> vs Te	Output Capacitan uency f = 1 MHz, per MII	Ce	9.0 012. t <sub>PHL</sub> vs C <sub>L</sub> = 50 p	pF	V <sub>CC</sub> = 5.0V	
6.00 5.00	measured at freq t <sub>PLH</sub> vs Te	Output Capacitan uency f = 1 MHz, per MII emperature (T <sub>A</sub> ) Output Switching	Ce	9.0 012. t <sub>PHL</sub> vs C <sub>L</sub> = 50 p 6.00	pF s Temperature (T F, 1 Output Swite	A) ching	
6.00 5.00 4.00	measured at freq t <sub>PLH</sub> vs Te	Output Capacitan uency f = 1 MHz, per MII emperature (T <sub>A</sub> ) Output Switching	Ce	9.0 1012. t <sub>PHL</sub> vs C <sub>L</sub> = 50 p 1.00	pF s Temperature (T F, 1 Output Swite	A) ching	

